

UNISONIC TECHNOLOGIES CO., LTD

UTT24N06 Power MOSFET

24A, 60V N-CHANNEL ENHANCEMENT MODE MOSFET

■ DESCRIPTION

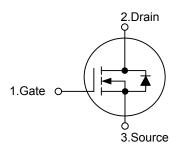
The UTC **UTT24N06** is an N-Channel enhancement mode MOSFET, it uses UTC's advanced technology to provide the customers with a minimum on state resistance and low gate charge, etc.

The UTC **UTT24N06** is suitable for switching application in Industry and converter application in LED TV, etc.

■ FEATURES

- * $R_{DS(ON)}$ < 40 m Ω @ V_{GS} =10V, I_{DS} =12A $R_{DS(ON)}$ < 50 m Ω @ V_{GS} =5V, I_{DS} =11A
- * Low R_{DS(ON)}

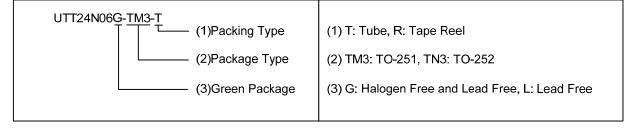
■ SYMBOL



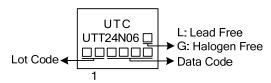
■ ORDERING INFORMATION

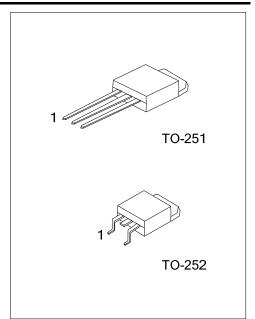
Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTT24N06L-TM3-T	UTT24N06G-TM3-T	TO-251	G	D	S	Tube	
UTT24N06L-TN3-R	UTT24N06G-TN3-R	TO-252	G	D	S	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



■ MARKING





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■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{ t DSS}$	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current	Continuous	I_{D}	24	Α
Pulsed Drain Current	Pulsed (Note 2)	I_{DM}	96	Α
Avalanche Current (Note 3)		I_{AR}	17.8	Α
Avalanche energy	Single Pulsed (Note 3)	E _{AS}	160	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	3.27	V/nS
Power Dissipation		P_D	60	W
Junction Temperature		T_J	+150	°C
Storage Temperature Range		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 3. L = 1.0mH, I_{AS} = 17.8A, V_{DD} = 50V, R_{G} = 25 Ω , Starting T_{J} = 25 $^{\circ}$ C
- 4. $I_{SD} \le 12A$, di/dt $\le 200A/\mu s$, $V_{DD} \le BV_{DSS}$, Starting $T_J = 25$ °C

THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient	θ_{JA}	110	°C/W	
Junction to Case	θ_{JC}	2.1	°C/W	

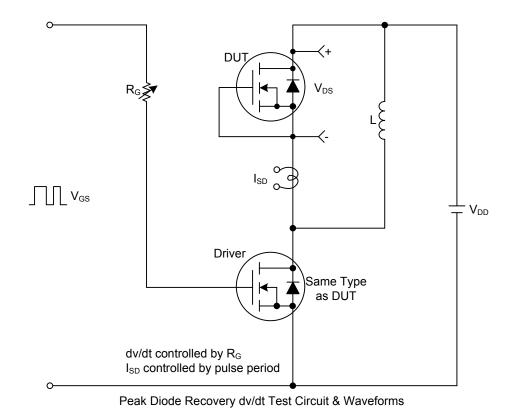
■ ELECTRICAL CHARACTERISTICS (T_J =25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT			
OFF CHARACTERISTICS									
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	60			V			
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =48V, V _{GS} =0V			1	μΑ			
Gate Leakage Current	I_{GSS}	V_{GS} =±20V, V_{DS} =0V			±100	nA			
ON CHARACTERISTICS									
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_{DS}=250\mu A$			3.0	V			
Drain-Source On-State Resistance		V _{GS} =10V, I _{DS} =12A			40	mΩ			
(Note 1)	$R_{DS(ON)}$	V _{GS} =5.0V, I _{DS} =11A			50	mΩ			
DYNAMIC PARAMETERS (Note 2)									
Input Capacitance	C _{ISS}			1080		pF			
Output Capacitance	Coss	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		130		pF			
Reverse Transfer Capacitance	C_{RSS}			85		pF			
SWITCHING PARAMETERS (Note 2)									
Total Gate Charge (Note 1)	Q_G	V _{DS} =30V, V _{GS} =10V, I _D =1.3A		115		nC			
Gate to Source Charge	Q_GS	$V_{DS}=30V$, $V_{GS}=10V$, $I_{D}=1.3A$ $-I_{G}=100\mu A$ (Note 1, 2)		6		nC			
Gate to Drain Charge	Q_GD			8		nC			
Turn-on Delay Time (Note 1)	$t_{D(ON)}$	V _{DS} =30V, V _{GS} =10V, I _D =0.5A,		36		ns			
Rise Time	t_R			49		ns			
Turn-off Delay Time	t _{D(OFF)}	R _G =25Ω (Note 1, 2)		320		ns			
Fall-Time	t_{F}			108		ns			
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS									
Maximum Body-Diode Continuous Current	I_S				12	Α			
Maximum Body-Diode Pulsed Current	I _{SM}				48	Α			
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	I _S =12A, V _{GS} =0V		0.8	1.3	V			
Reverse Recovery Time (Note 1)	t _{rr}	I _S =12A, V _{GS} =0V		124		ns			
Reverse Recovery Charge	Q_{rr}	dI _F /dt=100A/μs		165		μC			

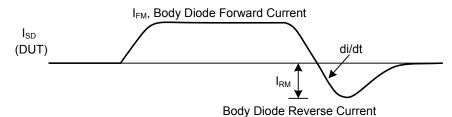
Notes: 1. Pulse Test: Pulse width ≤ 300µs, Duty cycle≤2%.

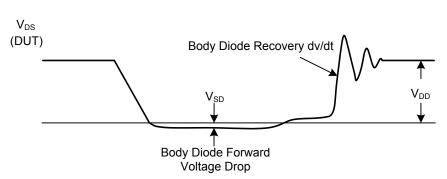
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

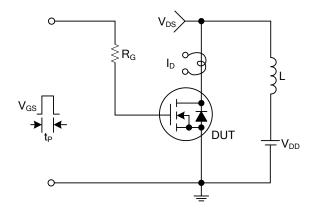


 V_{GS} (Driver) $D = \frac{\text{Gate Pulse Width}}{\text{Gate Pulse Period}}$ 10V

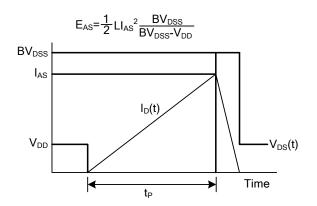




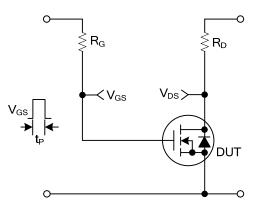
■ TEST CIRCUITS AND WAVEFORMS



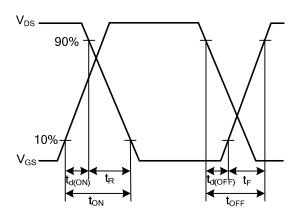
Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms



Resistive Switching Test Circuit



Resistive Switching Waveforms

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